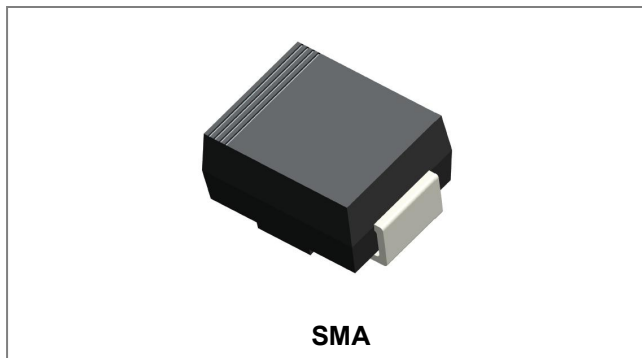


SES1D SURFACE MOUNT SUPER FAST RECTIFIER



Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Overload Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: Low Profile Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.06 grams(approx)

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	200	V
Average Rectified Forward Current	$I_F (AV)$	50% duty cycle @ $T_L=110^{\circ}C$, rectangular wave form	1	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3ms, Half Sine pulse	30	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 0.6A, Pulse, $T_J = 25^{\circ}C$ @ 1A, Pulse, $T_J = 25^{\circ}C$	0.865 0.92	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^{\circ}C$	5	μA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125^{\circ}C$	100	μA
Junction Capacitance	C_T	@ $V_R = 5V$, $T_C = 25^{\circ}C$ $f_{SIG} = 1MHz$	15	pF
Reverse Recovery Time	t_{rr}	$I_F=500mA$, $I_R=1A$, and $I_{rm}=250mA$	15	ns

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	75	°C/W
Approximate Weight	wt	-	0.09	g

Ratings and Characteristics Curves

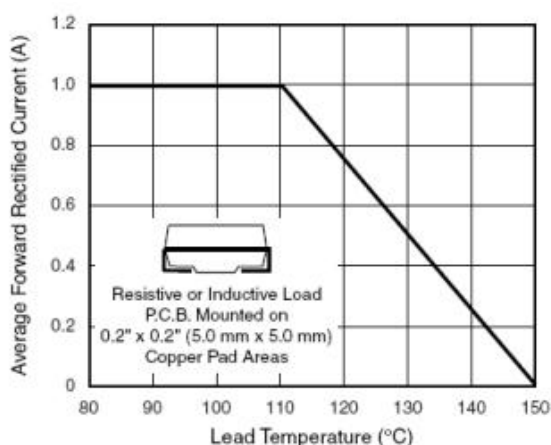


Fig. 1 - Maximum Forward Current Derating Curve

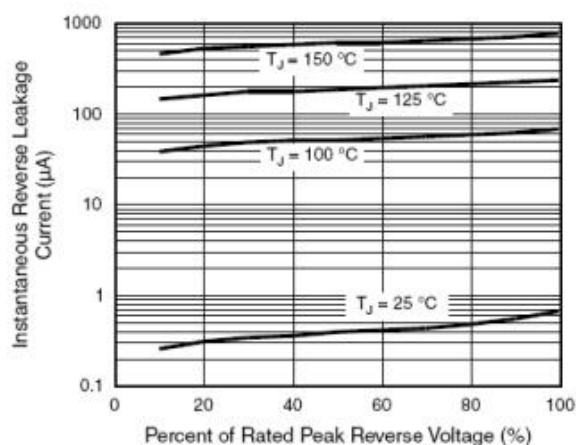


Fig. 4 - Typical Reverse Leakage Characteristics

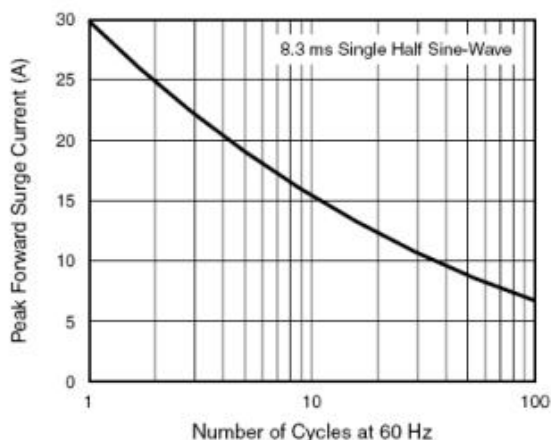


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

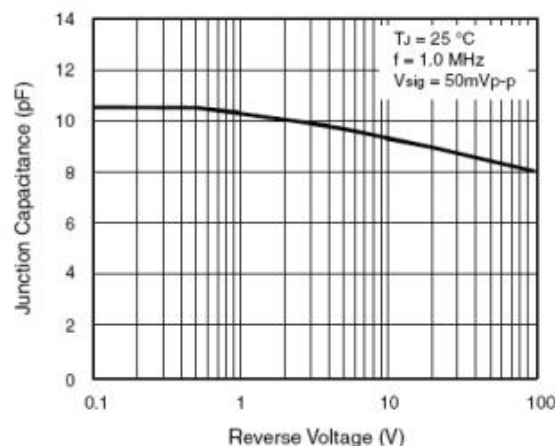
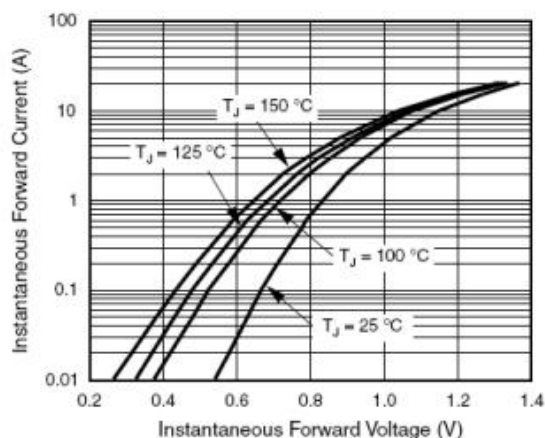
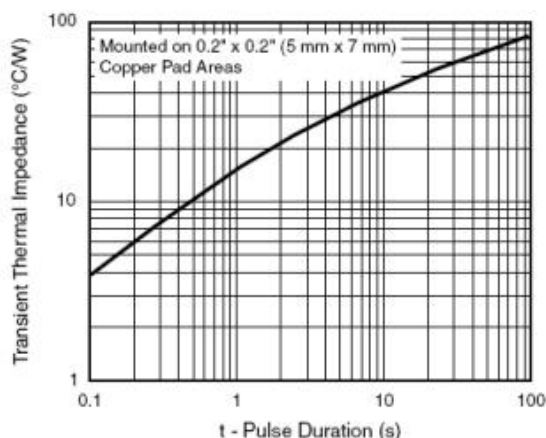
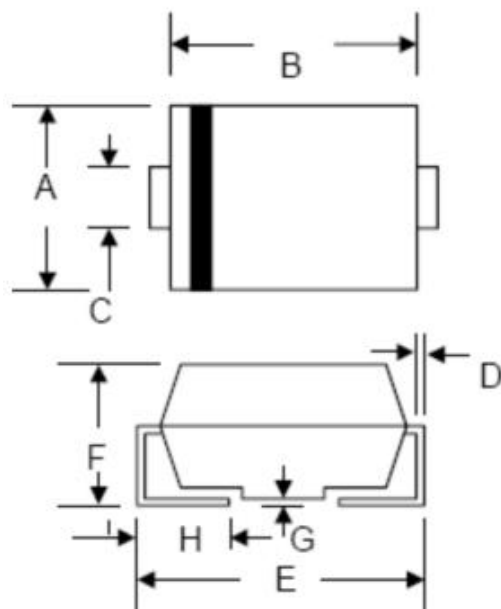


Fig. 5 - Typical Junction Capacitance


Fig. 3 - Typical Instantaneous Forward Characteristics

Fig. 6 - Typical Thermal Impedance

Mechanical Dimensions SMA



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.84	0.094	0.112
B	3.99	4.75	0.157	0.187
C	1.05	1.70	0.041	0.067
D	0.15	0.51	0.006	0.020
E	4.80	5.66	0.189	0.223
F	1.90	2.95	0.075	0.116
G	0.05	0.203	0.002	0.008
H	0.76	1.52	0.030	0.600

Ordering Information

Device	Package	Plating	Shipping
SES1D	SMA (Pb-Free)	Pure Sn	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

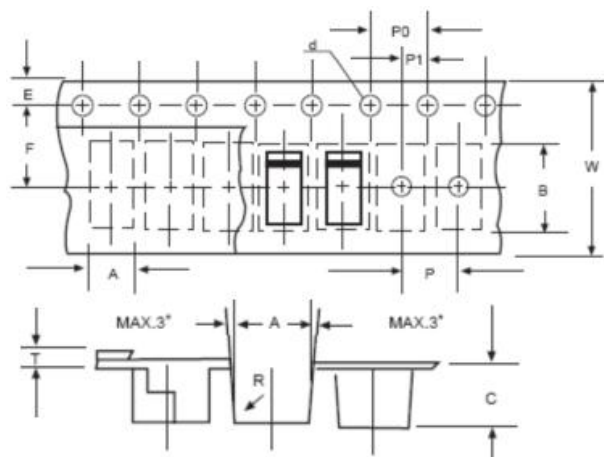


Where XXXXX is YYWWL

SES = Device Type
 1 = Forward Current (1A)
 D = Reverse Voltage (200V)
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Carrier Tape Specification SMA



SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

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